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Ordering number:EN5264

FX203

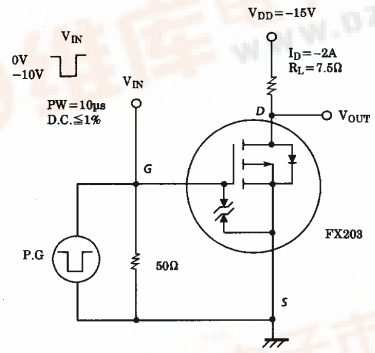
P-Channel Silicon MOSFET

Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- Low-voltage drive.

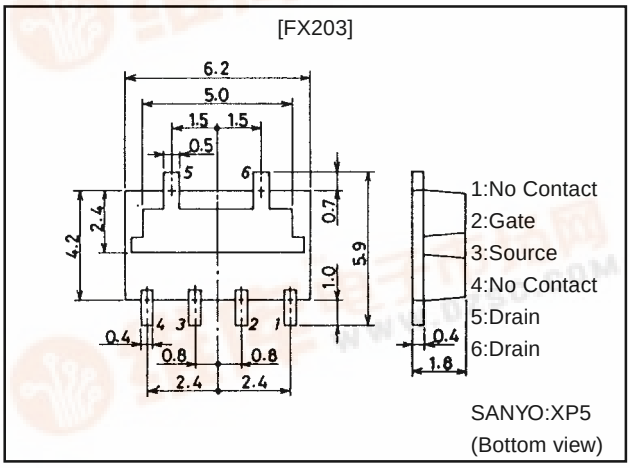
Switching Time Test CIrcuit



Package Dimensions

unit:mm

2121



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		–30	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		–4	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	–16	A
Allowable Power Dissipation	P_D	Tc=25˚C	8	W
	P_D	Mounted on ceramic board (750mm²×0.8mm)	2	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	I_D=–1mA, V_{GS}=0	–30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=–30V, V_{GS}=0			–100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=–10V, I_D=–1mA	–1.0		–2.5	V
Forward Transfer Admittance	$\lvert Y_{fs} \rvert$	V_{DS}=–10V, I_D=–2A	1.5	3		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	I_D=–2A, V_{GS}=–10V		120	160	mΩ
	$R_{DS(on)}$	I_D=–2A, V_{GS}=–4V		210	290	mΩ
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		370		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		230		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		70		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		10		ns
Rise Time	t_r	See specified Test Circuit		50		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		135		ns
Fall Time	t_f	See specified Test Circuit		125		ns
Diode Forward Voltage	V_{SD}	I_S=–4A, V_{GS}=0		–1.0	–1.2	V

- Marking:203

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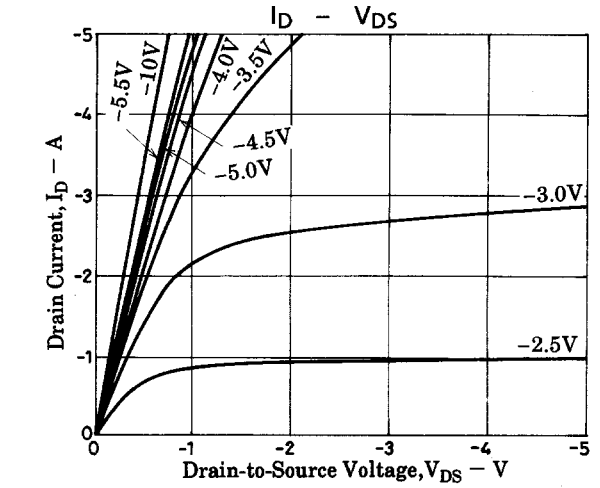
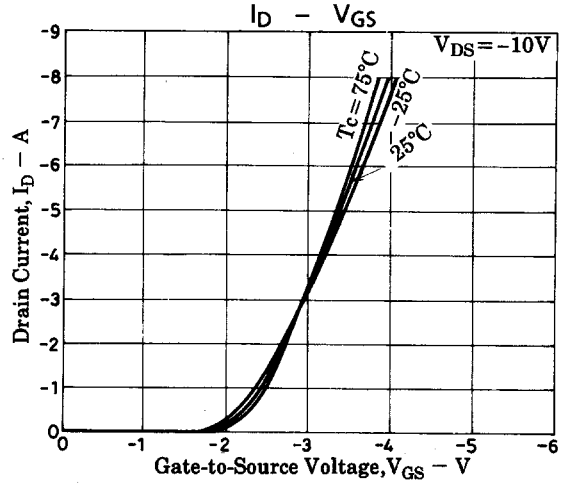
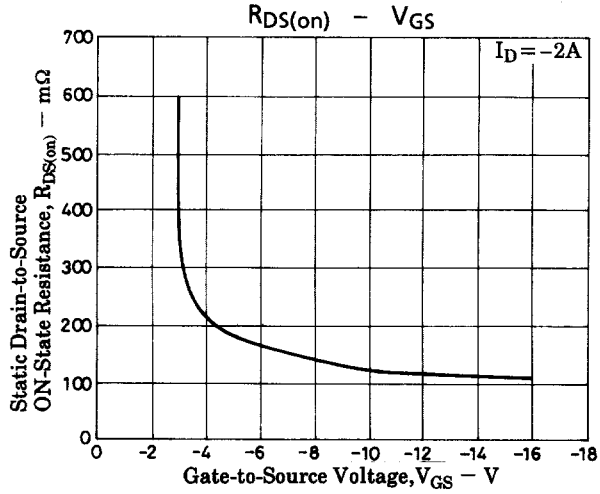
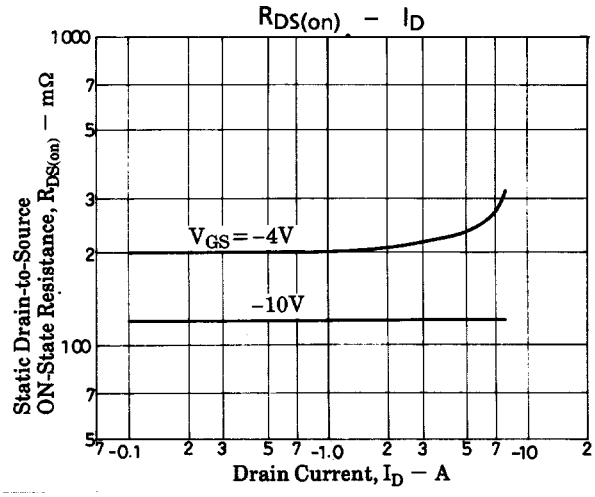
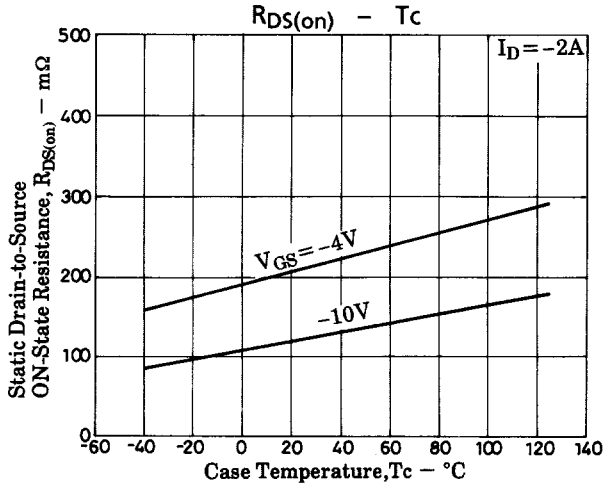
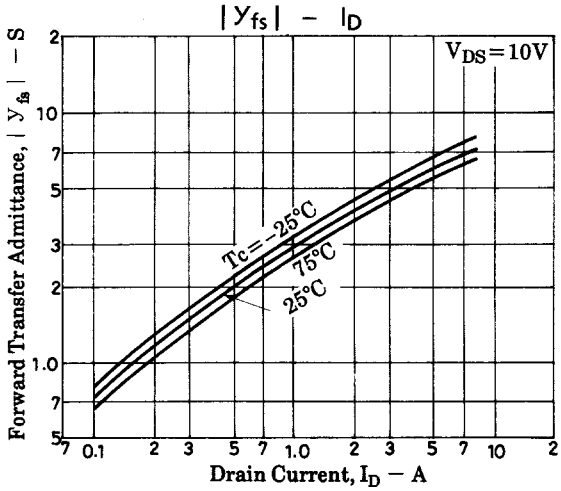

ID – VDS
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
–5.5V
–10V
–4.0V
–3.5V
–4.5V
–5.0V
–3.0V
–2.5V

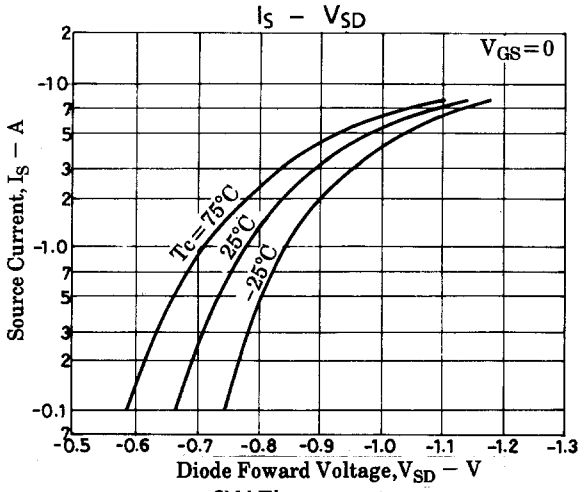

ID – VGS
VDS=–10V
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
Tc=75°C
–25°C
25°C

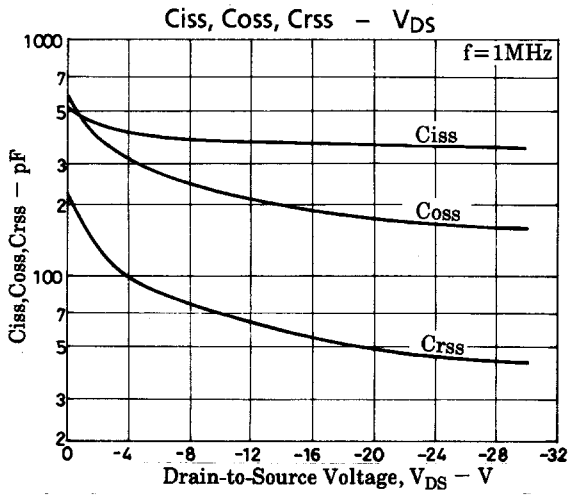

RDS(on) – VGS
ID=–2A
Static Drain-to-Source ON-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V

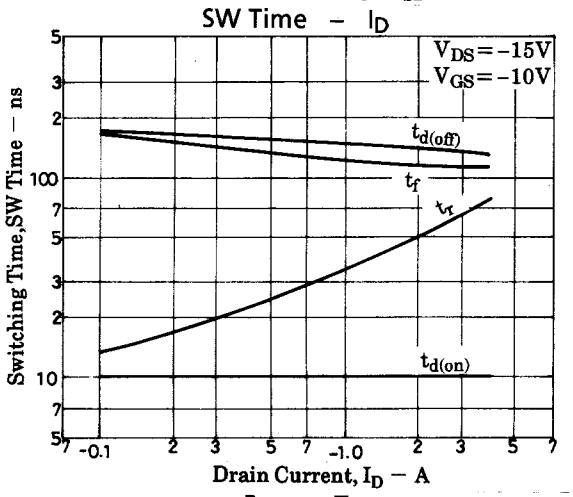

RDS(on) – ID
Static Drain-to-Source ON-State Resistance, RDS(on) – mΩ
VGS=–4V
–10V
Drain Current, ID – A

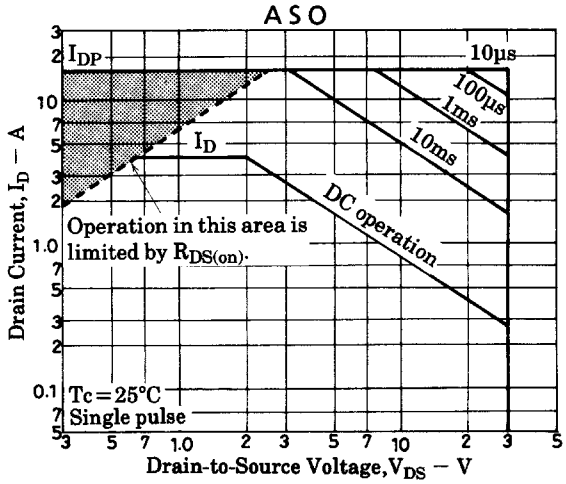

RDS(on) – Tc
ID=–2A
Static Drain-to-Source ON-State Resistance, RDS(on) – mΩ
VGS=–4V
–10V
Case Temperature, Tc – °C

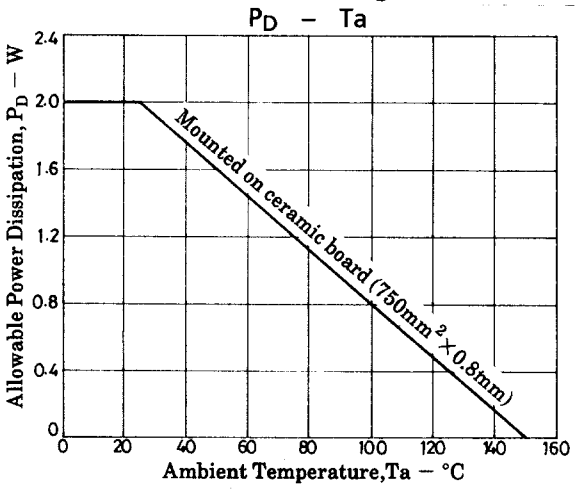

|yfs| – ID
VDS=10V
Forward Transfer Admittance, |yfs| – S
Tc=–25°C
75°C
25°C
Drain Current, ID – A

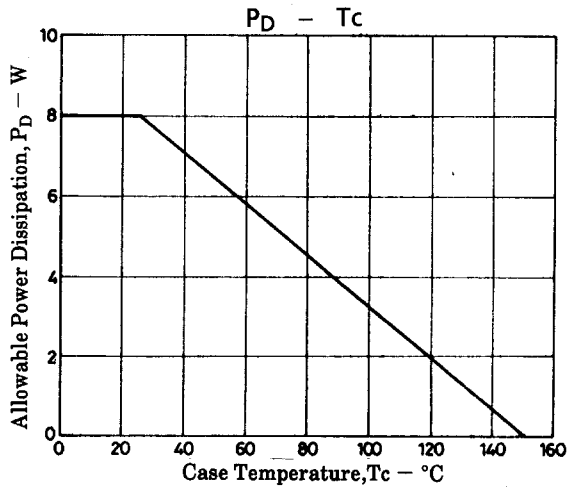












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